

<b>Notice of References Cited</b>				Application No. <b>08/799,506</b>		Applicant(s) <b>Yamazaki et al.</b>	
				Examiner <b>M. Wilczewski</b>		Group Art Unit <b>1107</b>	

  

U.S. PATENT DOCUMENTS						
	DOCUMENT NO.	DATE	NAME		CLASS	SUBCLASS
A	4,475,027	10/1984	Pressley		----	----
B	5,304,357	4/1994	Sato et al.		----	----
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N	2-73623	3/1990	JP	Aoyama et al.	----	----
O	1-76715	3/1989	JP	Sera	----	----
P	3-286518	12/1991	JP	Hashizume	----	----
Q	4-307727	10/1992	JP	Hashizume	----	----
R	2-255292	10/1990	JP	Imamura	----	----
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U	Wagner et al., "Formation of p-n Junctions and Silicides in Silicon Using a High Performance Laser Beam Homogenization System", Applied Surface Science, Vol. 43, 1989, pp. 260-263.	1989
V	Jhon et al., "Crystallization of Amorphous Silicon by Excimer Laser Annealing With a Line Shape Beam Having a Gaussian Profile", Jpn. J. Appl. Phys., Vol. 33, 1994, pp. L1438-L1441.	1994
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